

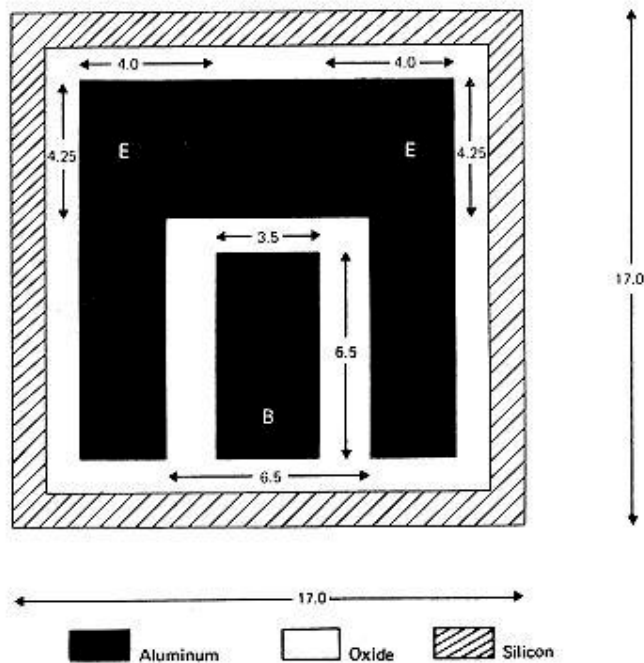
DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-897-7474



2N2222A 2N2221A
2N2219A 2N2218A
2N2222 2N2221
2N2219 2N2218

NPN SILICON
HIGH CURRENT (1.0 AMP) TRANSISTOR CHIPS
DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.



- Chip Thickness=6 Mils \pm 1 Mil
- Min. Dimension Across Bonding Pads=3.5 Mils
- Min. Separation Between Bonding Pads=1.5 Mils
- Distance from Bonding Pads to Edge of Chips=2.5 Mils

Detailed Specifications on Reverse Side

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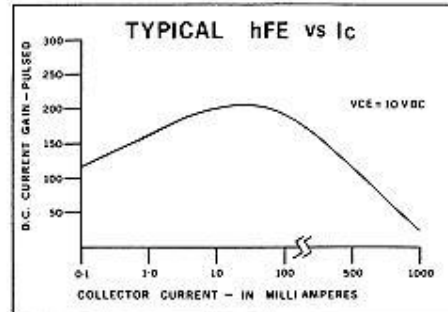


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NPN SILICON
HIGH CURRENT (1.0 AMP) TRANSISTOR CHIPS
DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.

IMPROVED GAIN AT HIGH CURRENT LEVELS • LOW LEAKAGE CHARACTERISTICS •
OVERSIZED BONDING PADS • NO BETA DEGRADATION DURING PROLONGED HIGH
TEMPERATURE ASSEMBLY •

The high efficiency parallel emitter construction provides improved beta retention at high current levels. The large area bonding pads are positioned for maximum flexibility of substrate layout. Unique surface stabilization processing results in lower leakage currents and prevents the beta degradation frequently encountered during the extended high temperature assembly operations required for complex hybrid circuit construction. Chips are gold backed for eutectic die-attach, and have aluminum bonding pads for all conventional wire bonding techniques.



← 100% Probe Tested to These Parameters @ 25°C → Guaranteed →
(tested on sample basis)

	h _{FE}			V _{CE0} Volts Min. @I _C = 10 _μ A I _E =0	V _{CE0} Volts Min. @I _C = 10mA I _E =0	V _{CE0} Volts Min. @I _C = 100A I _E =0	I _{CS0} nA Max. @V _{CE} as below I _E =0	V _{CC} (SAT.) Volts Max. @I _C =150mA I _E =15mA	C _{DE} pF Max. @V _{CE} =10V I _E =0 f=100KHz	f _T MHz Min. @I _C =20mA V _{CE} =20V f=100MHz
	@V _{CE} =10V @I _C = 1mA	@I _C = 10mA	@I _C = 150mA							
2N 2222A 2N 2219A	50 MIN	75 MIN	100- 300	70	40	6	10 @V _{CE} = 60V	0.4	8	250
2N 2221A 2N 2218A	25 MIN	35 MIN	40- 120							
2N 2222 2N 2219	50 MIN	75 MIN	100- 300	60	30	5	10 @V _{CE} = 50V	0.4	8	250
2N 2221 2N 2218	25 MIN	35 MIN	40- 120							

Dimensional Drawing on Reverse Side

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